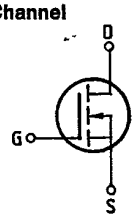
SIEMENS AKTIENGESELLSCHAF

## Main ratings

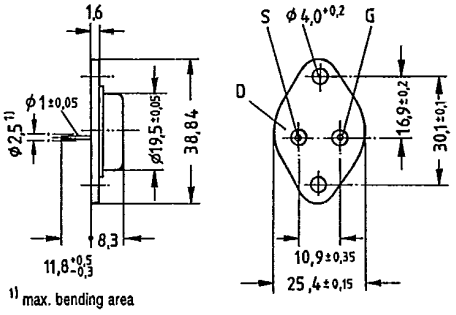
| | | |
|---|---|---|
| Drain-source voltage | $V_{DS}$ | = 800 V |
| Continuous drain current | $I_D$ | = 3,4 A |
| Drain-source on-resistance | $R_{DS(on)}$ | = 3,0 Ω |

N-Channel




**Description** SIPMOS, N-channel, enhancement mode
**Case** Metal case 3 A 2 in accordance with DIN 41 872, or TO 204 AA (TO 3) in accordance with JEDEC. Approx. weight 12 g

| Type | Ordering code |
|---|---|
| S BUZ 83 A | C67078-A1012-A3 |




1) max. bending area

Dimensions in mm

## Maximum ratings

| Description | Symbols | Ratings | Units | Conditions |
|---|---|---|---|---|
| Drain-source voltage | $V_{DS}$ | 800 | V | |
| Drain-gate voltage | $V_{DGR}$ | 800 | V | $R_{GS}$ = 20 kΩ |
| Continuous drain current | $I_D$ | 3,4 | A | $T_C$ = 25 °C |
| Pulsed drain current | $I_{Dpuls}$ | 11 | A | $T_C$ = 25 °C |
| Gate-source voltage | $V_{GS}$ | ±20 | V | |
| Max. power dissipation | $P_D$ | 78 | W | $T_C$ = 25 °C |
| Operating and storage temperature range | $T_j$ $T_{stg}$ | −55 ... +150 | °C | |
| DIN humidity category | | C | – | DIN 40040 |
| IEC climatic category | | 55/150/56 | | DIN IEC 68-1 |
| **Thermal resistance** | | | | |
| Chip – case | $R_{th\,JC}$ | ≤1,6 | K/W | |
| Chip – ambient | $R_{th\,JA}$ | ≤35 | K/W | |

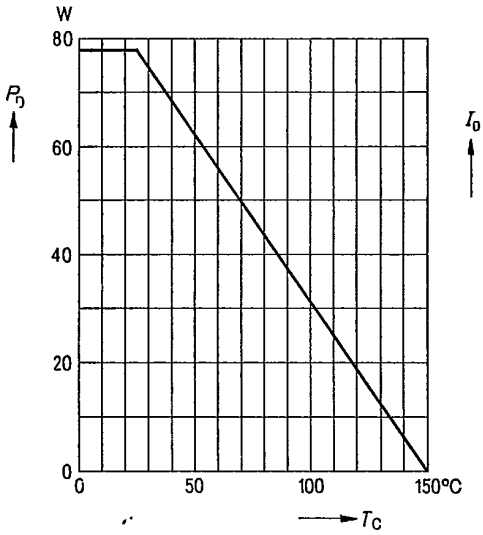
 S Preferred Type

## Electrical characteristics

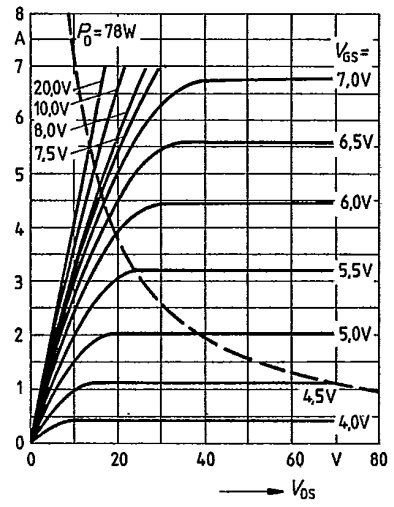
(at $T_j$ = 25 °C unless otherwise specified)

| Description | Symbol | Characteristics min. | typ. | max. | Unit | Conditions |
|---|---|---|---|---|---|---|
| **Static ratings** | | | | | | |
| Drain-source breakdown voltage | $V_{(BR)\,DSS}$ | 800 | – | – | V | $V_{GS}$ = 0V<br>$I_D$ = 0,25mA |
| Gate threshold voltage | $V_{GS\,(th)}$ | 2,1 | 3,0 | 4,0 | | $V_{DS}$ = $V_{GS}$<br>$I_D$ = 1mA |
| Zero gate voltage drain current | $I_{DSS}$ | –<br>– | 20<br>100 | 250<br>1000 | µA | $T_j$ = 25 °C<br>$T_j$ = 125 °C<br>$V_{DS}$ = 800V<br>$V_{GS}$ = 0V |
| Gate-source leakage current | $I_{GSS}$ | – | 10 | 100 | nA | $V_{GS}$ = 20V<br>$V_{DS}$ = 0V |
| Drain-source on-resistance | $R_{DS\,(on)}$ | – | 2,7 | 3,0 | Ω | $V_{GS}$ = 10V<br>$I_D$ = 1,7A |
| **Dynamic ratings** | | | | | | |
| Forward transconductance | $g_{fs}$ | 1,0 | 1,8 | – | S | $V_{DS}$ = 25V<br>$I_D$ = 1,7A |
| Input capacitance | $C_{iss}$ | – | 1,6 | 2,1 | nF | $V_{GS}$ = 0V<br>$V_{DS}$ = 25V<br>$f$ = 1MHz |
| Output capacitance | $C_{oss}$ | – | 90 | 150 | pF | |
| Reverse transfer capacitance | $C_{rss}$ | – | 30 | 55 | | |
| Turn-on time $t_{on}$ ($t_{on} = t_{d\,(on)} + t_r$) | $t_{d\,(on)}$ | – | 30 | 45 | ns | $V_{CC}$ = 30V<br>$I_D$ = 2,3A<br>$V_{GS}$ = 10V<br>$R_{GS}$ = 50Ω |
| | $t_r$ | – | 40 | 60 | | |
| Turn-off time $t_{off}$ ($t_{off} = t_{d\,(off)} + t_f$) | $t_{d\,(off)}$ | – | 110 | 140 | | |
| | $t_f$ | – | 60 | 80 | | |
| **Reverse diode** | | | | | | |
| Continuous reverse drain current | $I_{DR}$ | – | – | 3,4 | A | $T_C$ = 25 °C |
| Pulsed reverse drain current | $I_{DRM}$ | – | – | 13 | | |
| Diode forward on-voltage | $V_{SD}$ | – | 1,1 | 1,35 | V | $I_F$ = 2 × $I_{DR}$<br>$V_{GS}$ = 0V, $T_j$ = 25 °C |
| Reverse recovery time | $t_{rr}$ | – | 1800 | – | ns | $T_j$ = 25 °C<br>$I_F$ = $I_{DR}$<br>$d_{iF/dt}$ = 100A/µs<br>$V_R$ = 100V |
| Reverse recovery charge | $Q_{rr}$ | – | 12 | – | µC | |

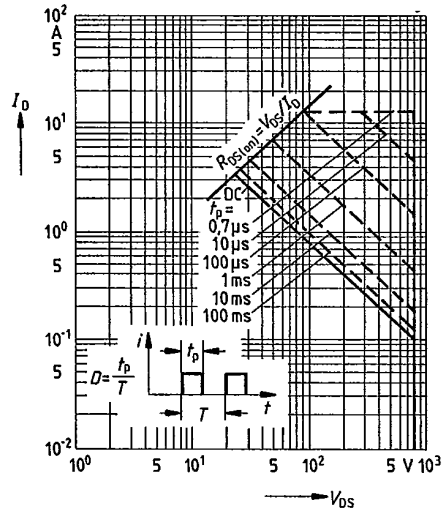
**Power dissipation** $P_D = f(T_C)$



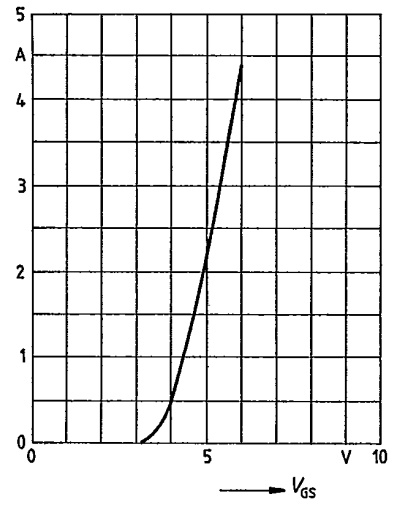

**Typical output characteristics** $I_D = f(V_{DS})$
parameter: 80 µs pulse test,
$T_j = 25°C$



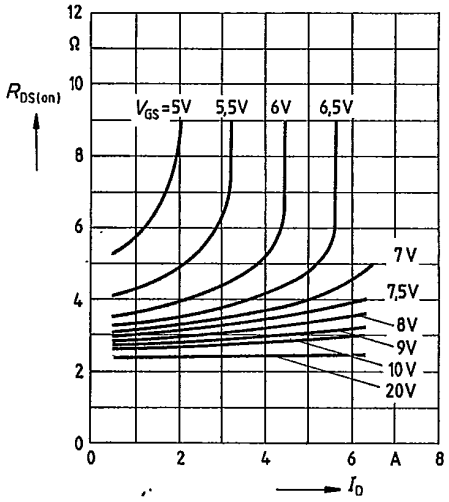

**Safe operating area** $I_D = f(V_{DS})$
parameter: $D = 0.01$, $T_C = 25°C$



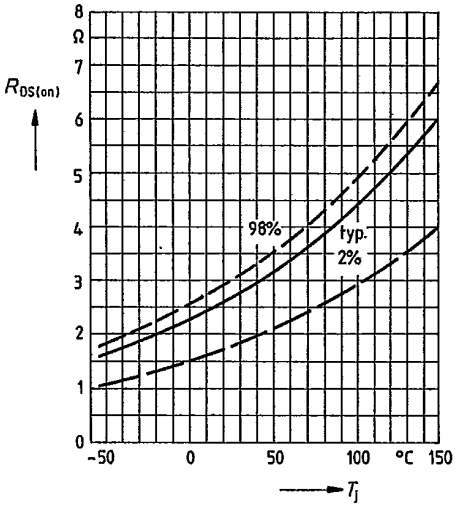

**Typical transfer characteristic** $I_D = f(V_{GS})$
parameter: 80 µs pulse test,
$V_{DS} = 25V$, $T_j = 25°C$



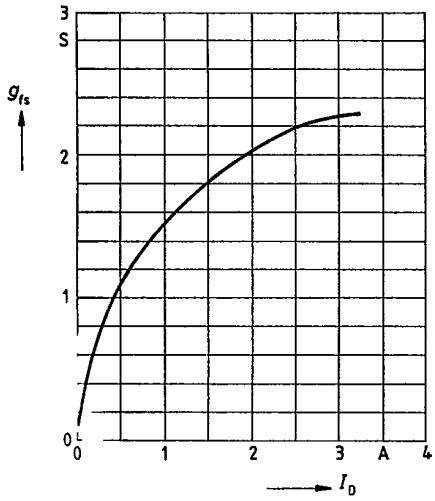
**Typical drain-source on-state resistance**
$R_{DS\,(on)} = f(I_D)$
parameter: $V_{GS}$; $T_j$ = 25 °C



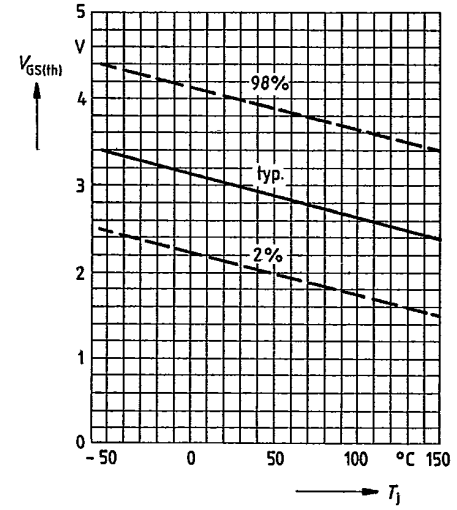

**Drain-source on-state resistance**
$R_{DS\,(on)} = f(T_j)$
parameter: $I_D$ = 1,7A, $V_{GS}$ = 10V
(spread)




**Typical transconductance** $g_{fs} = f(I_D)$
parameter: 80 µs pulse test,
$V_{DS}$ = 25V, $T_j$ = 25 °C




**Gate threshold voltage** $V_{GS(th)} = f(T_j)$
parameter: $V_{DS} = V_{GS}$, $I_D$ = 1mA
(spread)



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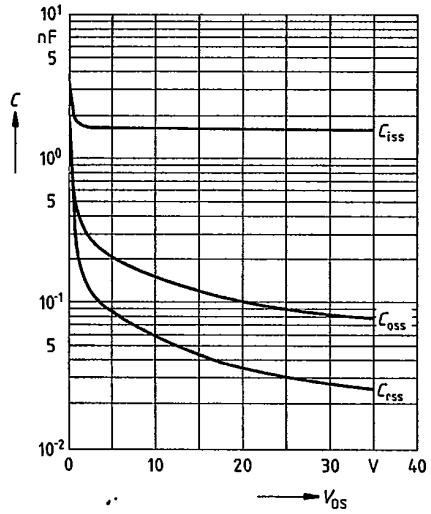
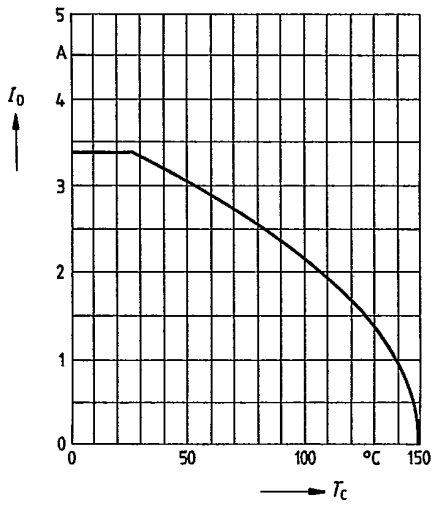
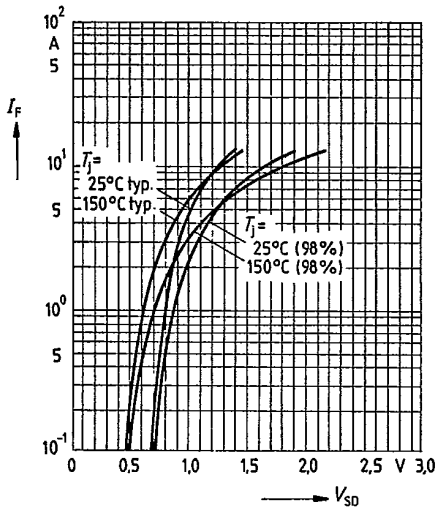
**Typical capacitances $C = f(V_{DS})$**
parameter: $V_{GS} = 0$, $f = 1$MHz



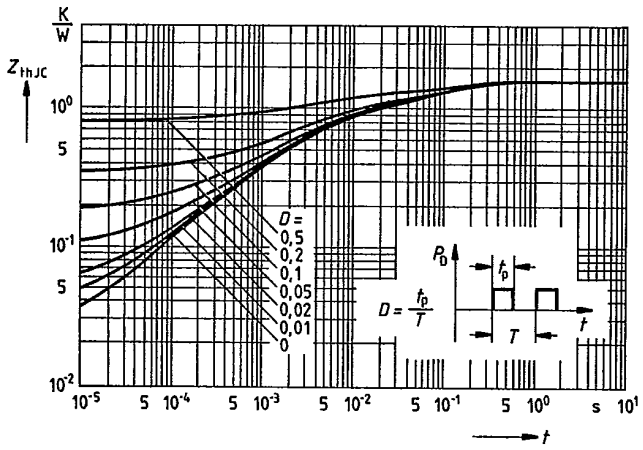

**Continuous drain current $I_D = f(T_C)$**
parameter: $V_{GS} \geq 10$V




**Forward characteristic of reverse diode**
$I_F = f(V_{SD})$
parameter: $T_j$, $t_p = 80$ µs
(spread)



**Transient thermal impedance $Z_{thJC} = f(t)$**
**parameter: $D = t_p / T$**




**Typical gate-charge $V_{GS} = f(Q_{Gate})$**
**parameter: $I_{D\,puls} = 5A$**